

Silicon NPN Power Transistors

2SC2902

DESCRIPTION

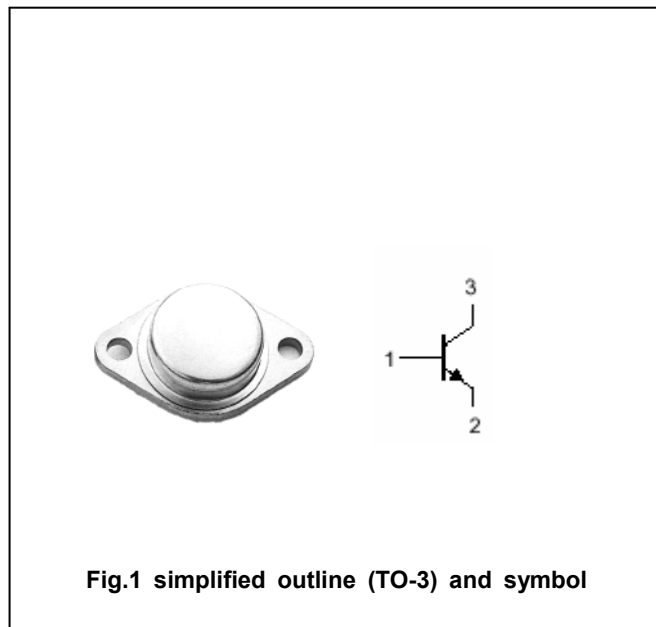
- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor controls

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	800	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	9	V
I_C	Collector current		15	A
I_{CM}	Collector current-Peak		30	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	150	W
T_j	Junction temperature		200	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~200	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=0.1A$; $I_B=0$; $L=25mH$	400			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA$; $I_C=0$	9			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=7.5A$; $I_B=2.5A$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=7.5A$; $I_B=2.5A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=640V$; $I_E=0$			50	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=9V$; $I_C=0$			50	μA
h_{FE}	DC current gain	$I_C=7.5A$; $V_{CE}=5V$	10		35	

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PACKAGE OUTLINE

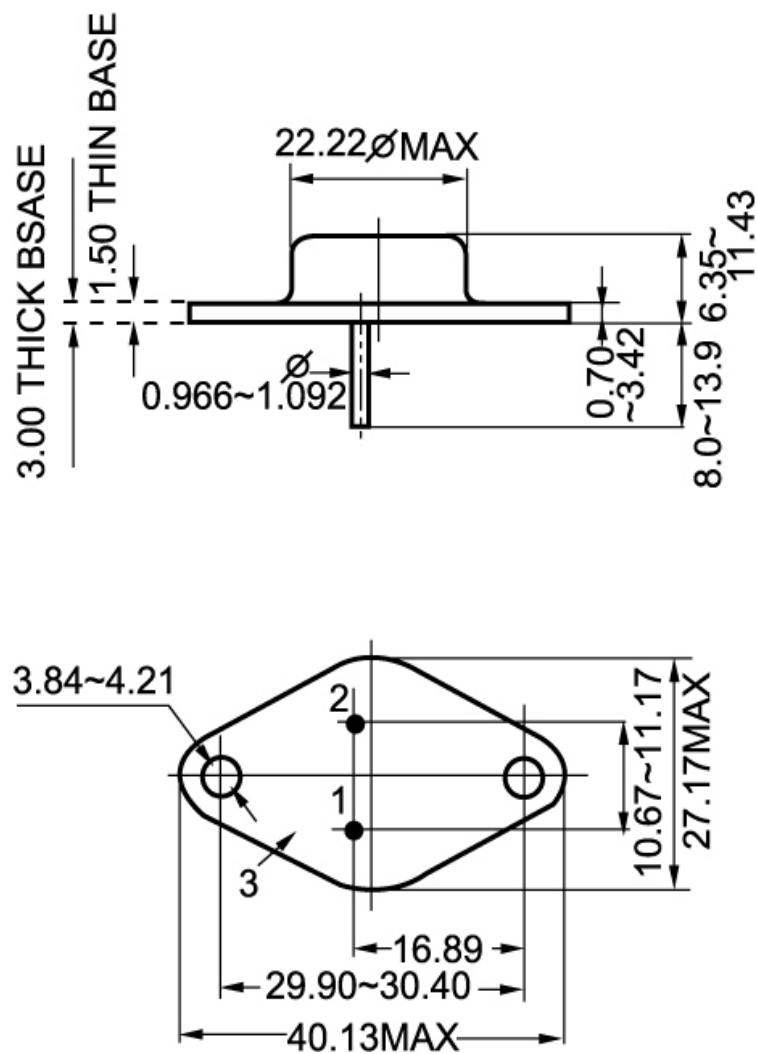


Fig.2 Outline dimensions